

NP60N04MUK, NP60N04NUK

R07DS0597EJ0200

Rev.2.00

MOS FIELD EFFECT TRANSISTOR

May 24, 2018

Description

These products are N-channel MOS Field Effect Transistors designed for high current switching applications.

Features

- Super low on-state resistance
 $R_{DS(on)} = 4.3 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 30 \text{ A)}$
- Low C_{iss} : $C_{iss} = 2450 \text{ pF TYP. (} V_{DS} = 25 \text{ V)}$
- Designed for automotive application and AEC-Q101 qualified

Ordering Information

Part No.	Lead Plating	Packing	Package
NP60N04MUK-S18-AY *1	Pure Sn (Tin)	Tube 50 p/tube	TO-220 (MP-25K)
NP60N04NUK-S18-AY *1			TO-262 (MP-25SK)

Note: *1 Pb-free (This product does not contain Pb in the external electrode)

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	40	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 60	A
Drain Current (pulse) *1, 3	$I_{D(pulse)}$	± 240	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T1}	105	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T2}	1.8	W
Channel Temperature	T_{ch}	175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 175	$^\circ\text{C}$
Repetitive Avalanche Current *2, 3	I_{AR}	28	A
Repetitive Avalanche Energy *2, 3	E_{AR}	78	mJ

Thermal Resistance

Channel to Case Thermal Resistance	$R_{th(ch-C)}$ *3	1.43	$^\circ\text{C/W}$
Channel to Ambient Thermal Resistance	$R_{th(ch-A)}$ *3	83.3	$^\circ\text{C/W}$

Notes: *1 $T_C = 25^\circ\text{C}$, $P_w \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

*2 $R_G = 25 \Omega$, $V_{GS} = 20 \rightarrow 0 \text{ V}$

*3 Not subject of production test. Verified by design/characterization.

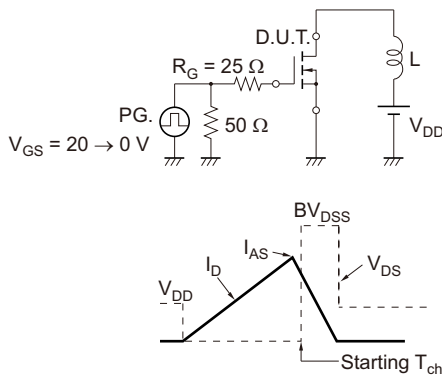
Electrical Characteristics ($T_A = 25^\circ\text{C}$)

Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$
Gate Leakage Current	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$
Gate to Source Threshold Voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$
Forward Transfer Admittance *1	$ y_{fs} $	22	44	—	S	$V_{DS} = 5\text{ V}, I_D = 30\text{ A}$
Drain to Source On-state Resistance *1	$R_{DS(on)}$	—	3.6	4.3	$\text{m}\Omega$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$
Input Capacitance *2	C_{iss}	—	2450	3680	pF	$V_{DS} = 25\text{ V}$ $V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}$
Output Capacitance *2	C_{oss}	—	340	510	pF	
Reverse Transfer Capacitance *2	C_{rss}	—	140	260	pF	
Turn-on Delay Time *2	$t_{d(on)}$	—	19	50	ns	$V_{DD} = 20\text{ V}, I_D = 30\text{ A}$ $V_{GS} = 10\text{ V}$ $R_G = 0\ \Omega$
Rise Time *2	t_r	—	9	30	ns	
Turn-off Delay Time *2	$t_{d(off)}$	—	45	90	ns	
Fall Time *2	t_f	—	7	20	ns	
Total Gate Charge *2	Q_G	—	42	63	nC	$V_{DD} = 32\text{ V}$
Gate to Source Charge	Q_{GS}	—	11	—	nC	$V_{GS} = 10\text{ V}$
Gate to Drain Charge	Q_{GD}	—	11	—	nC	$I_D = 60\text{ A}$
Body Diode Forward Voltage *1	$V_{F(S-D)}$	—	0.9	1.5	V	$I_F = 60\text{ A}, V_{GS} = 0\text{ V}$
Reverse Recovery Time	t_{rr}	—	44	—	ns	$I_F = 60\text{ A}, V_{GS} = 0\text{ V}$
Reverse Recovery Charge	Q_{rr}	—	40	—	nC	$di/dt = 100\text{ A}/\mu\text{s}$

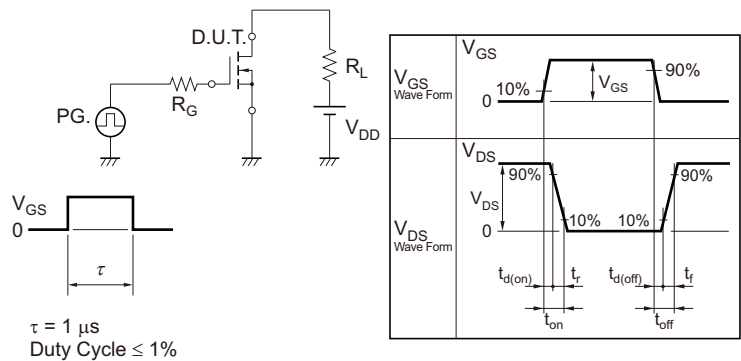
Note: *1 Pulsed test

Note: *2 Not subject of production test. Verified by design/characterization.

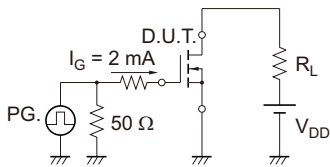
TEST CIRCUIT 1 AVALANCHE CAPABILITY



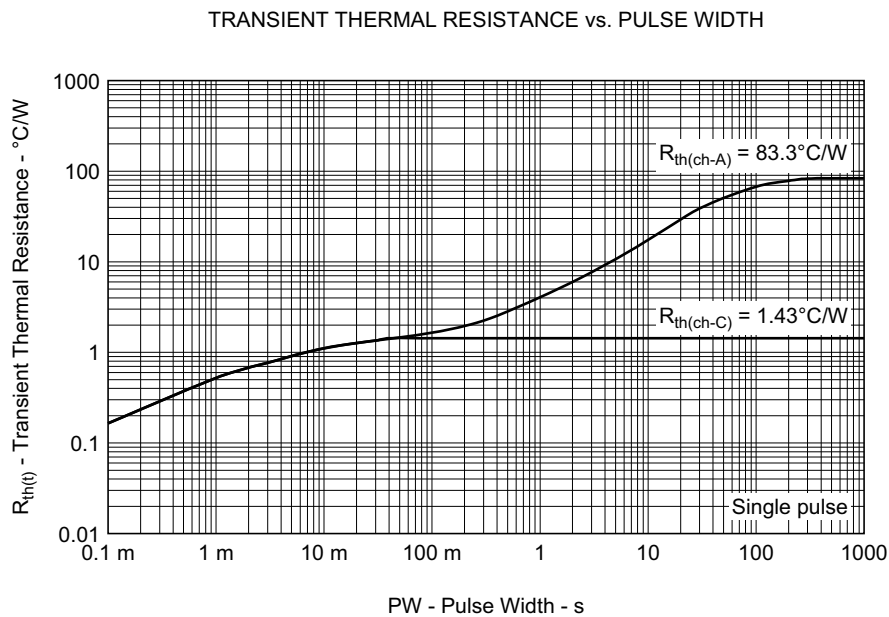
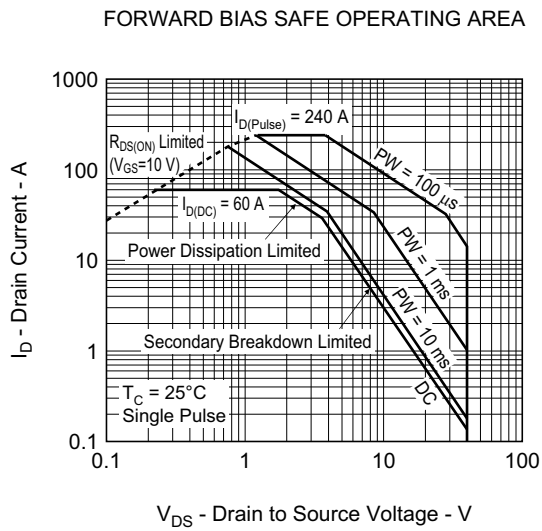
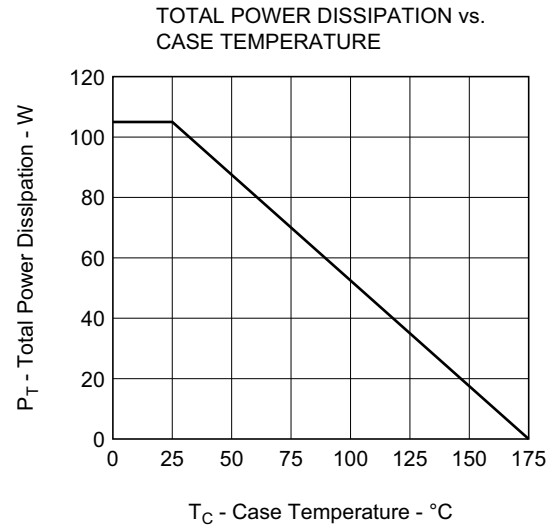
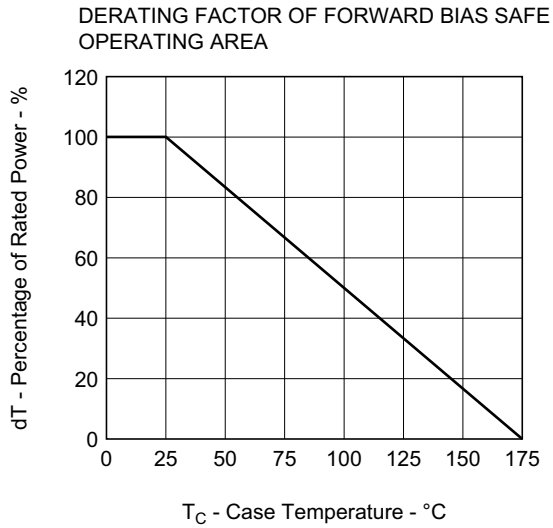
TEST CIRCUIT 2 SWITCHING TIME



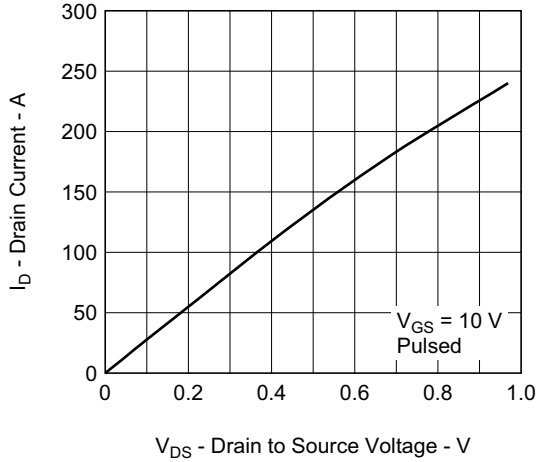
TEST CIRCUIT 3 GATE CHARGE



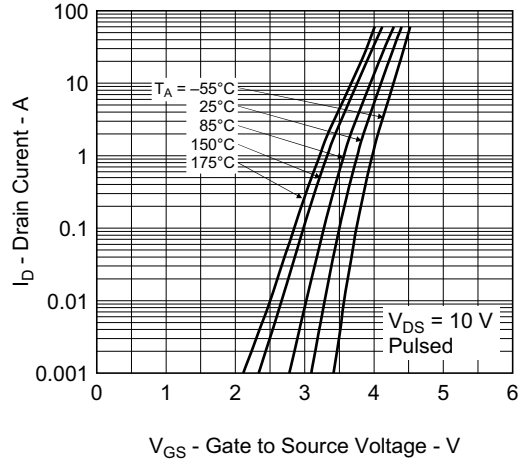
Typical Characteristics ($T_A = 25^\circ\text{C}$)



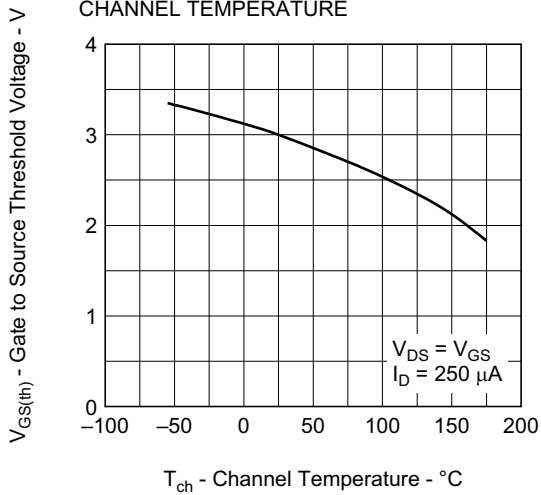
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



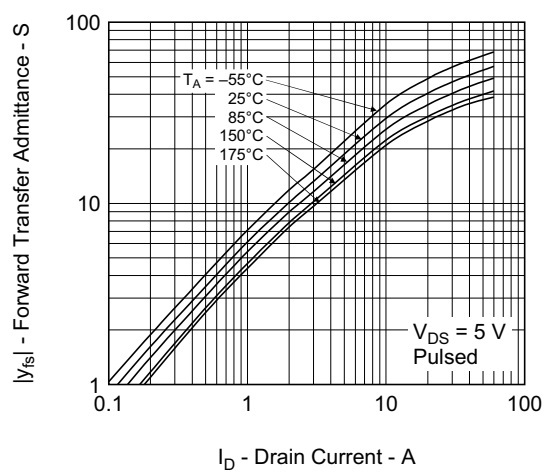
FORWARD TRANSFER CHARACTERISTICS



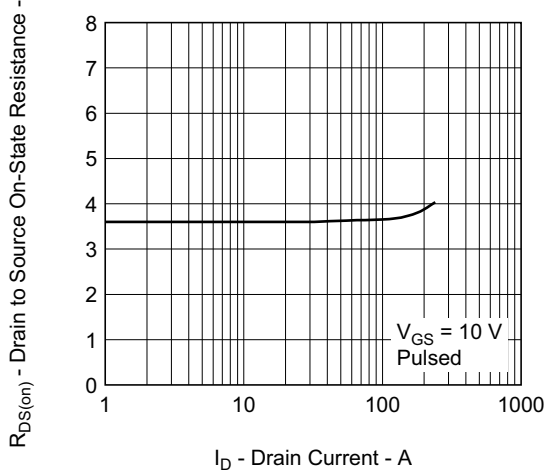
GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE



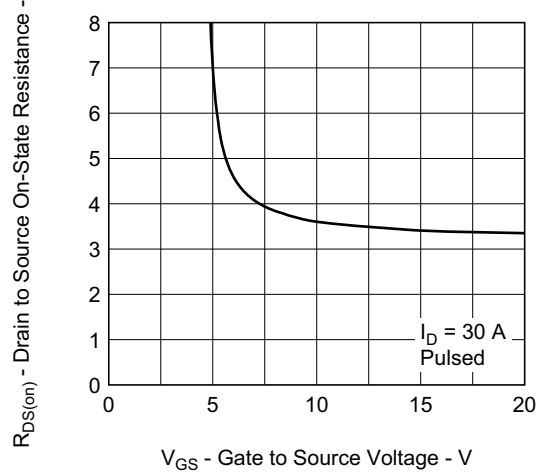
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



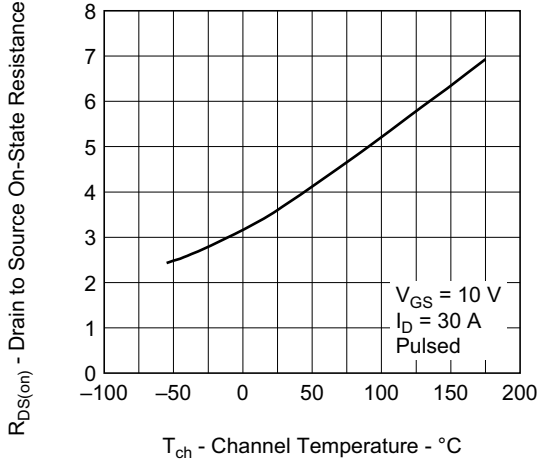
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



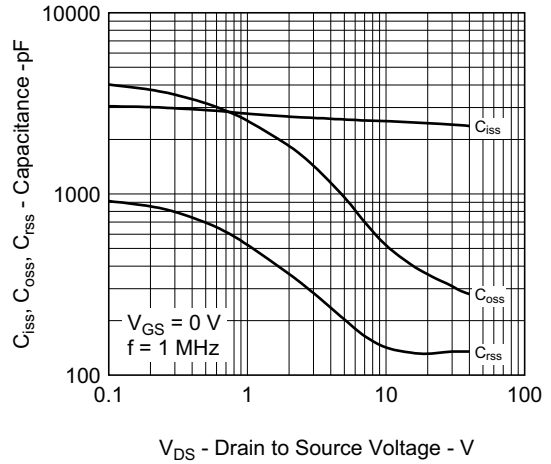
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



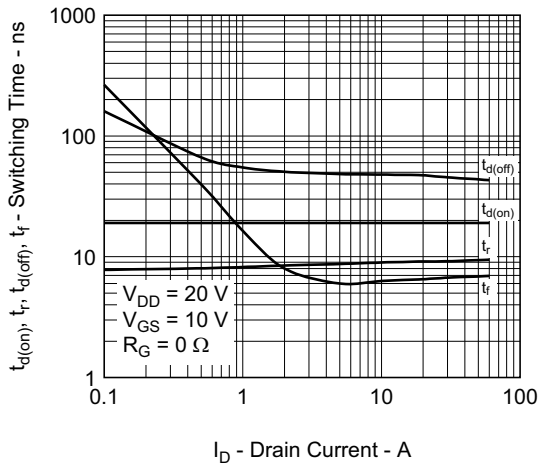
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



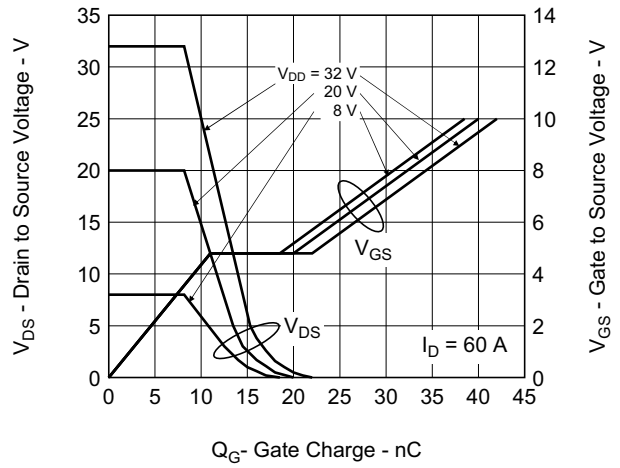
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



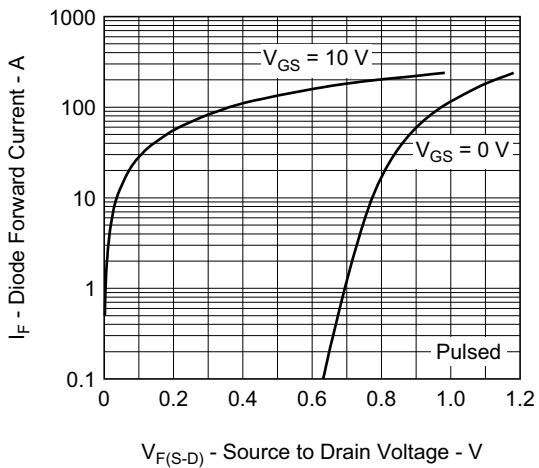
SWITCHING CHARACTERISTICS



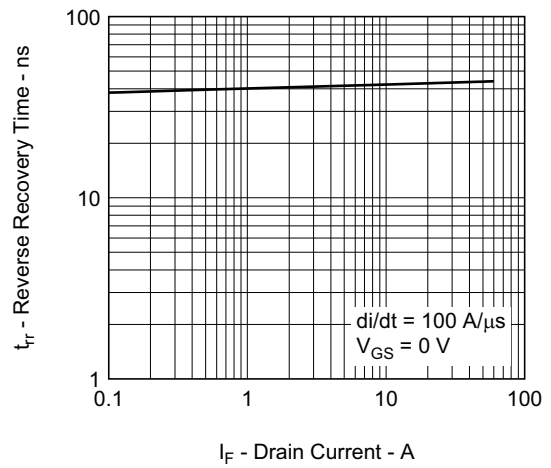
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

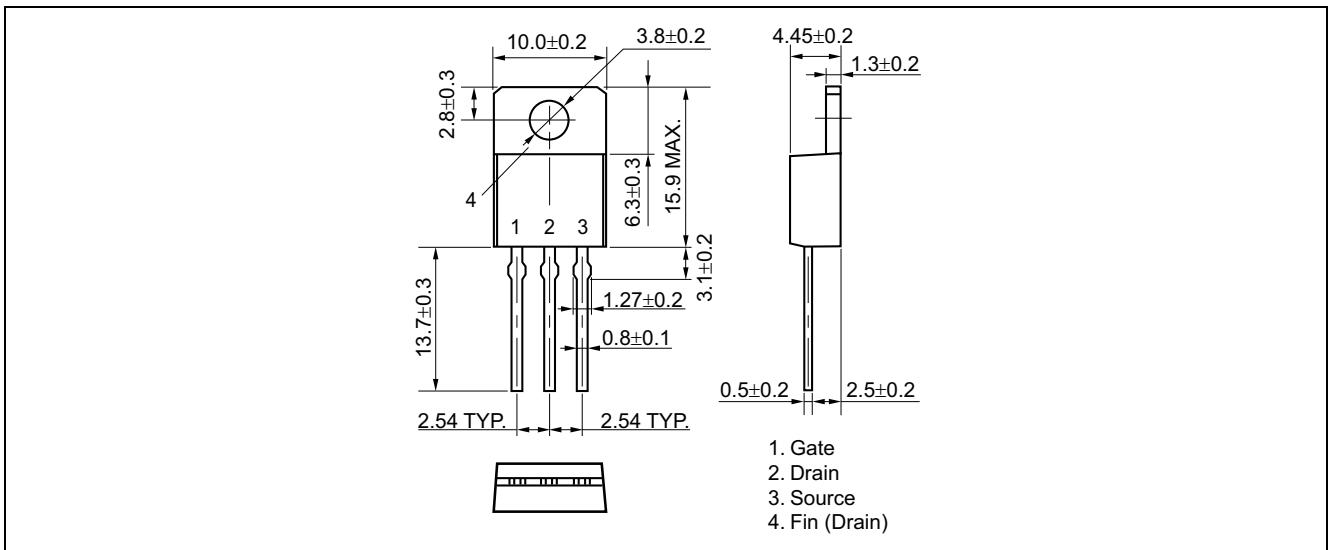


REVERSE RECOVERY TIME vs. DRAIN CURRENT

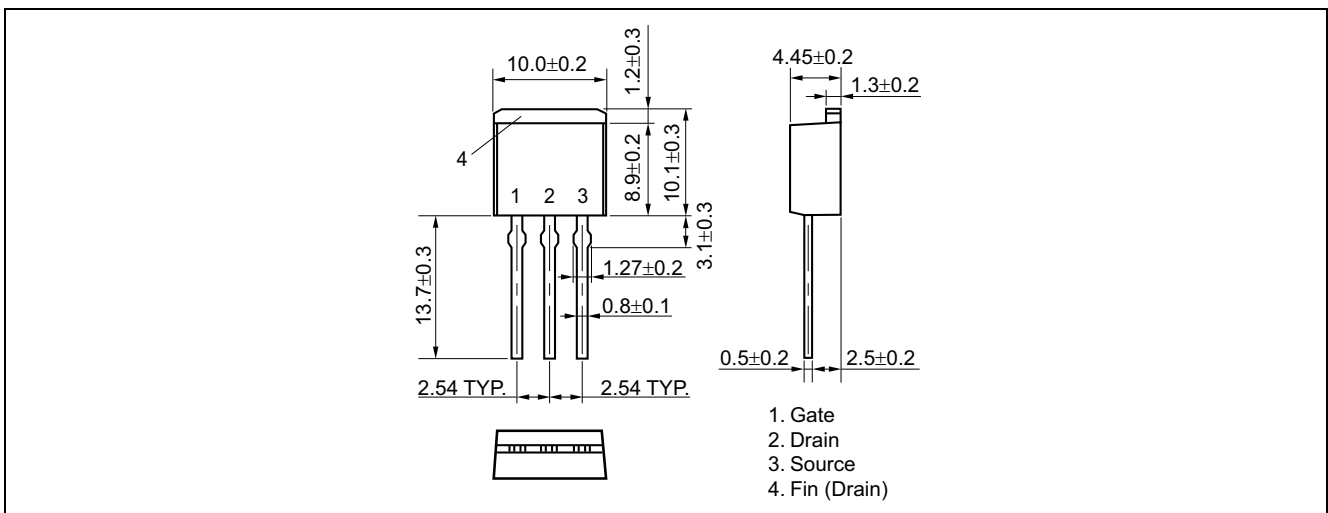


Package Drawing (Unit: mm)

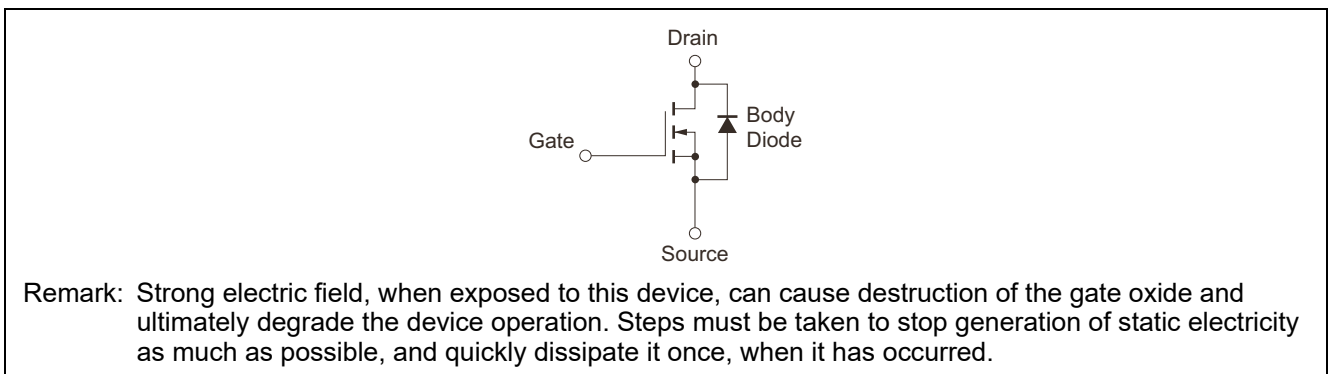
TO-220 (MP-25K) (Mass: 1.9 g TYP.)



TO-262 (MP-25SK) (Mass: 1.8 g TYP.)



Equivalent Circuit



Revision History	NP60N04MUK, NP60N04NUK Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Jan 11, 2012	—	First Edition Issued
2.00	May 24 ,2018	1	Note 3 was added
		2	Note 2 was added

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